## 1. General description

Enhanced ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

## 2. Features and benefits

- High thermal cycling performance
- Low thermal resistance
- Low on-state losses
- Soft recovery characteristic


## 3. Applications

- Dual Mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology


## 4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Values |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Absolute maximum rating |  |  |  |  |  |  |
| $\mathrm{V}_{\text {RRM }}$ | repetitive peak reverse voltage |  | 600 |  |  | V |
| $\mathrm{I}_{\text {F(AV) }}$ | average forward current | $\delta=0.5$; square-wave pulse; $\mathrm{T}_{\mathrm{mb}} \leq 115{ }^{\circ} \mathrm{C}$; <br> Fig. 1; Fig. 2 | 9 |  |  | A |
| $\mathrm{I}_{\text {fRM }}$ | repetitive peak forward current | $\delta=0.5 ; \mathrm{t}_{\mathrm{p}}=25 \mu \mathrm{~s} ; \mathrm{T}_{\mathrm{mb}} \leq 115^{\circ} \mathrm{C} ;$ <br> square-wave pulse | 18 |  |  | A |
| $\mathrm{I}_{\text {FSM }}$ | non-repetitive peak forward current | $\mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms} ; \mathrm{T}_{\text {j(init) }}=25^{\circ} \mathrm{C}$; sine-wave pulse; Fig. 3 | 91 |  |  | A |
|  |  | $\mathrm{t}_{\mathrm{p}}=8.3 \mathrm{~ms} ; \mathrm{T}_{\text {j(init) }}=25^{\circ} \mathrm{C}$; sine-wave pulse | 100 |  |  | A |
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| Static characteristics |  |  |  |  |  |  |
| $V_{F}$ | forward voltage | $\mathrm{I}_{\mathrm{F}}=8 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} ;$ Fig. 5 | - | 1.45 | 1.9 | V |
|  |  | $\mathrm{I}_{\mathrm{F}}=8 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$; Fig. 5 | - | 1.25 | 1.7 | V |
| Dynamic characteristics |  |  |  |  |  |  |
| $\mathrm{t}_{\text {r }}$ | reverse recovery time | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=30 \mathrm{~V} ; \mathrm{dl}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s} ; \\ & \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} ; \text { Fig. } 6 \end{aligned}$ | - | 17.5 | 35 | ns |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| :---: | :---: | :---: | :---: | :---: |
| 1 | K | cathode |  | $\mathrm{K} \underset{\text { o01aaa020 }}{\underset{\sim}{\gtrless}} \mathrm{A}$ |
| 2 | A | anode |  |  |
| mb | mb | mounting base; cathode |  |  |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |  |  |
| :--- | :--- | :--- | :--- |
|  | Name | Description | Version |
| BYV29F-600 | TO-220AC | plastic single-ended package; heatsink mounted; <br> 1 mounting hole; 2-lead TO-220AC | SOD59 |

## 7. Marking

Table 4. Marking codes

| Type number | Marking codes |
| :--- | :--- |
| BYV29F-600 | BYV29F-600 |

## 8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {RRM }}$ | repetitive peak reverse voltage |  | 600 | V |
| $\mathrm{V}_{\text {RWM }}$ | crest working reverse voltage |  | 600 | V |
| $V_{R}$ | reverse voltage | DC | 600 | V |
| $\mathrm{I}_{\text {F(AV) }}$ | average forward current | $\delta=0.5 ; \text { square-wave pulse; } \mathrm{T}_{\mathrm{mb}} \leq 115^{\circ} \mathrm{C} \text {; }$ $\text { Fig. 1; Fig. } 2$ | 9 | A |
| $\mathrm{I}_{\text {FRM }}$ | repetitive peak forward current | $\delta=0.5 ; \mathrm{t}_{\mathrm{p}}=25 \mu \mathrm{~s} ; \mathrm{T}_{\mathrm{mb}} \leq 115^{\circ} \mathrm{C} ;$ <br> square-wave pulse | 18 | A |
| $\mathrm{I}_{\text {FSM }}$ | non-repetitive peak forward current | $\mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms} ; \mathrm{T}_{\text {j(fint) }}=25^{\circ} \mathrm{C}$; sine-wave pulse; Fig. 3 | 91 | A |
|  |  | $\mathrm{t}_{\mathrm{p}}=8.3 \mathrm{~ms} ; \mathrm{T}_{\text {j(init) }}=25^{\circ} \mathrm{C}$; sine-wave pulse | 100 | A |
| $\mathrm{T}_{\text {stg }}$ | storage temperature |  | -40 to 150 | ${ }^{\circ} \mathrm{C}$ |
| T | junction temperature |  | 150 | ${ }^{\circ} \mathrm{C}$ |



Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$a=$ form factor $=I_{\text {F(RMS) }} / I_{\text {FAV) }}$
Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions |  | Min | Typ | Max | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{R}_{\text {th( }(\text {-mb })}$ | thermal resistance <br> from junction to <br> mounting base | Fig 4 |  | - | - | 2.5 | K/W |
| $\mathrm{R}_{\text {th(i-a) }}$ | thermal resistance <br> from junction to <br> ambient free air | in free air |  | - | 60 | - | K/W |



Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

## 10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Static characteristics |  |  |  |  |  |  |
| $V_{\text {F }}$ | forward voltage | $\mathrm{I}_{\mathrm{F}}=8 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; Fig. 5 | - | 1.45 | 1.9 | V |
|  |  | $\mathrm{I}_{\mathrm{F}}=8 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=150{ }^{\circ} \mathrm{C} ;$ Fig. 5 | - | 1.25 | 1.7 | V |
| $I_{R}$ | reverse current | $V_{R}=600 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=100^{\circ} \mathrm{C}$ | - | - | 1.5 | mA |
|  |  | $\mathrm{V}_{\mathrm{R}}=600 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | - | 50 | $\mu \mathrm{A}$ |
| Dynamic characteristics |  |  |  |  |  |  |
| $\mathrm{Q}_{\mathrm{r}}$ | recovered charge | $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=30 \mathrm{~V} ; \mathrm{dI}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s}$ | - | 13 | - | nC |
| $\mathrm{t}_{\text {tr }}$ | reverse recovery time | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=1 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=30 \mathrm{~V} ; \mathrm{dI}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s} ; \\ & \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} ; \underline{\text { Fig. } 6} \end{aligned}$ | - | 17.5 | 35 | ns |
| $\mathrm{I}_{\mathrm{RM}}$ | peak reverse recovery current | $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=30 \mathrm{~V} ; \mathrm{dI}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s} ;$ <br> Fig. 6 | - | 1.5 | - | A |
| $V_{\text {FR }}$ | forward recovery voltage | $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~A} ; \mathrm{dl}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s} ;$ Fig. 7 | - | 3.2 | - | V |


(1) $\mathrm{T}_{\mathrm{i}}=150^{\circ} \mathrm{C}$; typical values
(2) $T_{j}=150^{\circ} \mathrm{C}$; maximum values
(3) $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; maximum values

Fig. 5. Forward current as a function of forward voltage


Fig. 6. Reverse recovery definitions; ramp recovery


Fig. 7. Forward recovery definitions

## 11. Package outline



## 12. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| :--- | :--- | :--- | :--- | :--- | :--- |
| BYV29F-600 v. 3 | 20180228 | Product data sheet | - | BYV29F-600 v.2 |
| Modifications: | Change from NXP version to WeEn version | BYV29F-600 v. 1 |  |  |
| BYV29F-600 v.2 | 20110307 | Product data sheet | - | - |
| Modifications: | Various changes to content. | Product data sheet | - |  |
| BYV29F-600 v.1 | 20100907 |  |  |  |

## 13. Legal information

## Data sheet status

| Document <br> status [1][2] | Product <br> status [3] | Definition |
| :--- | :--- | :--- |
| Objective <br> [short] data <br> sheet | Development | This document contains data from <br> the objective specification for product <br> development. |
| Preliminary <br> [short] data <br> sheet | Qualification | This document contains data from the <br> preliminary specification. |
| Product <br> [short] data <br> sheet | Production | This document contains the product <br> specification. |

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2] The term 'short data sheet' is explained in section "Definitions".
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